

Modeling Material Plastic and Viscous Flow Effects in TSV-middle and Backside TSV-last Processes

Aditya Karmarkar¹, Xiaopeng Xu¹, Karim El Sayed¹

Wei Guo², Geert Van der Plas², Stefaan Van Huylenbroeck²,
Mario Gonzalez², Philippe Absil², Eric Beyne²

¹Synopsys, Inc., Mountain View, California, USA

²IMEC, Kapeldreef 75, Leuven, Belgium

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Agenda

Introduction

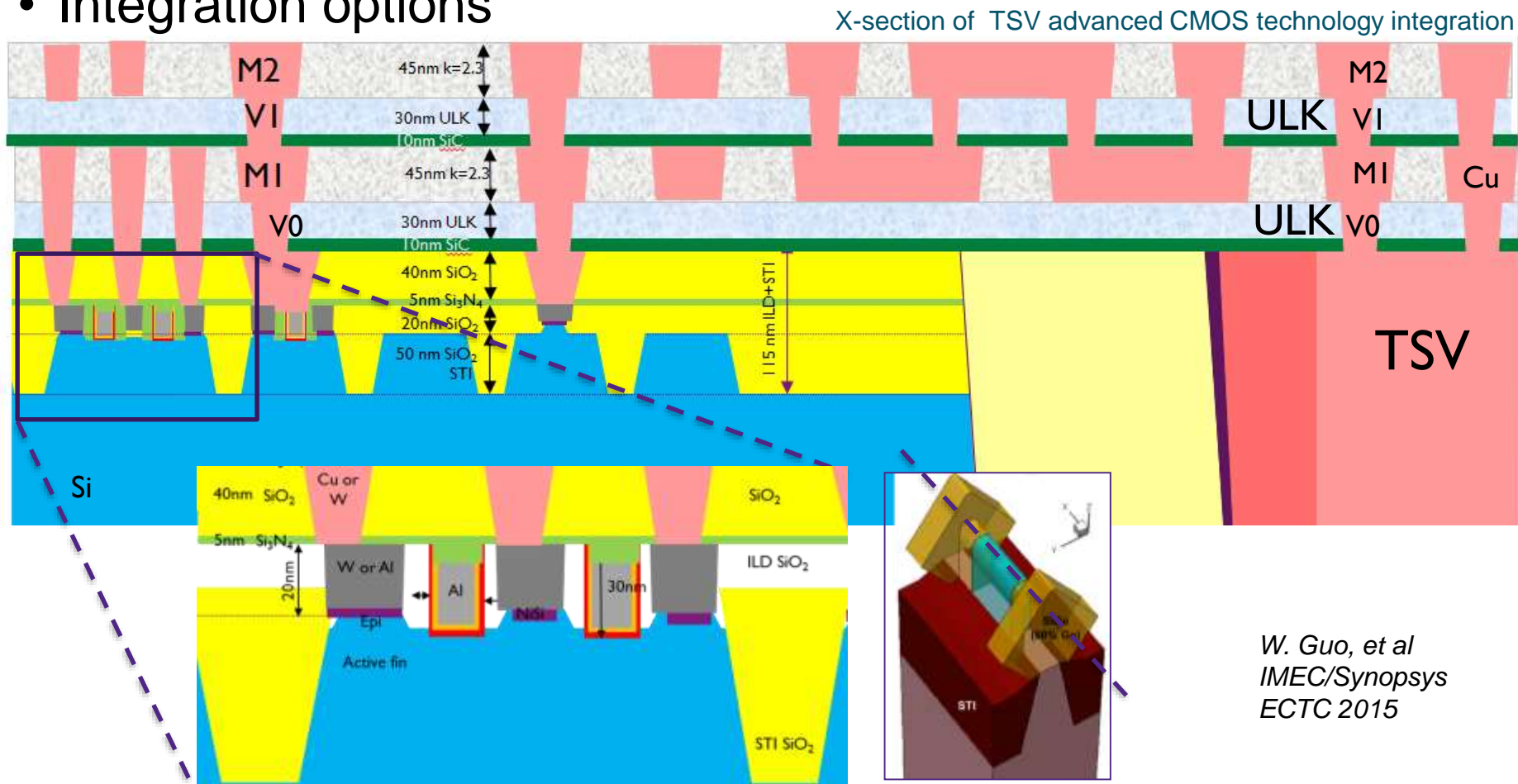
Material model characterization

TSV stress effects on performance and reliability

Summary

Introduction: TSV integration

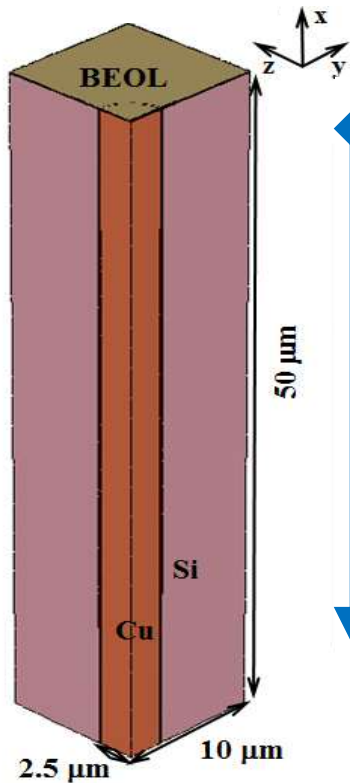
- 3D IC with TSV: provides high integration density; allows heterogeneous integration, improves system performance
- Integration options



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TSV-middle Integration Sample Flow

- TSV-middle: via processed after FEOL and before BEOL
- High thermal budget is expected



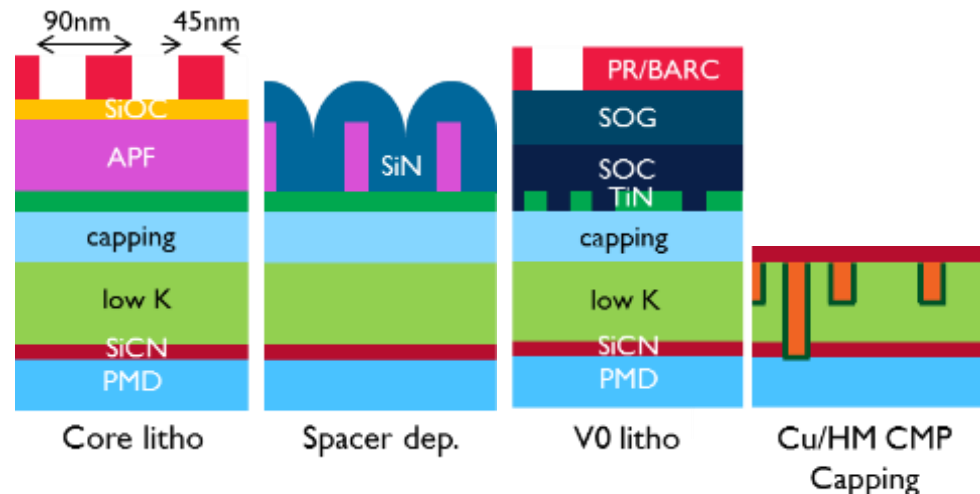
TSV-middle process

FEOL process
 TSV etching
 TSV liner/Barrier
 TSV plating
 420°C 1h annealing
 TSV CMP
 BEOL process

 Backside process
 Stacking

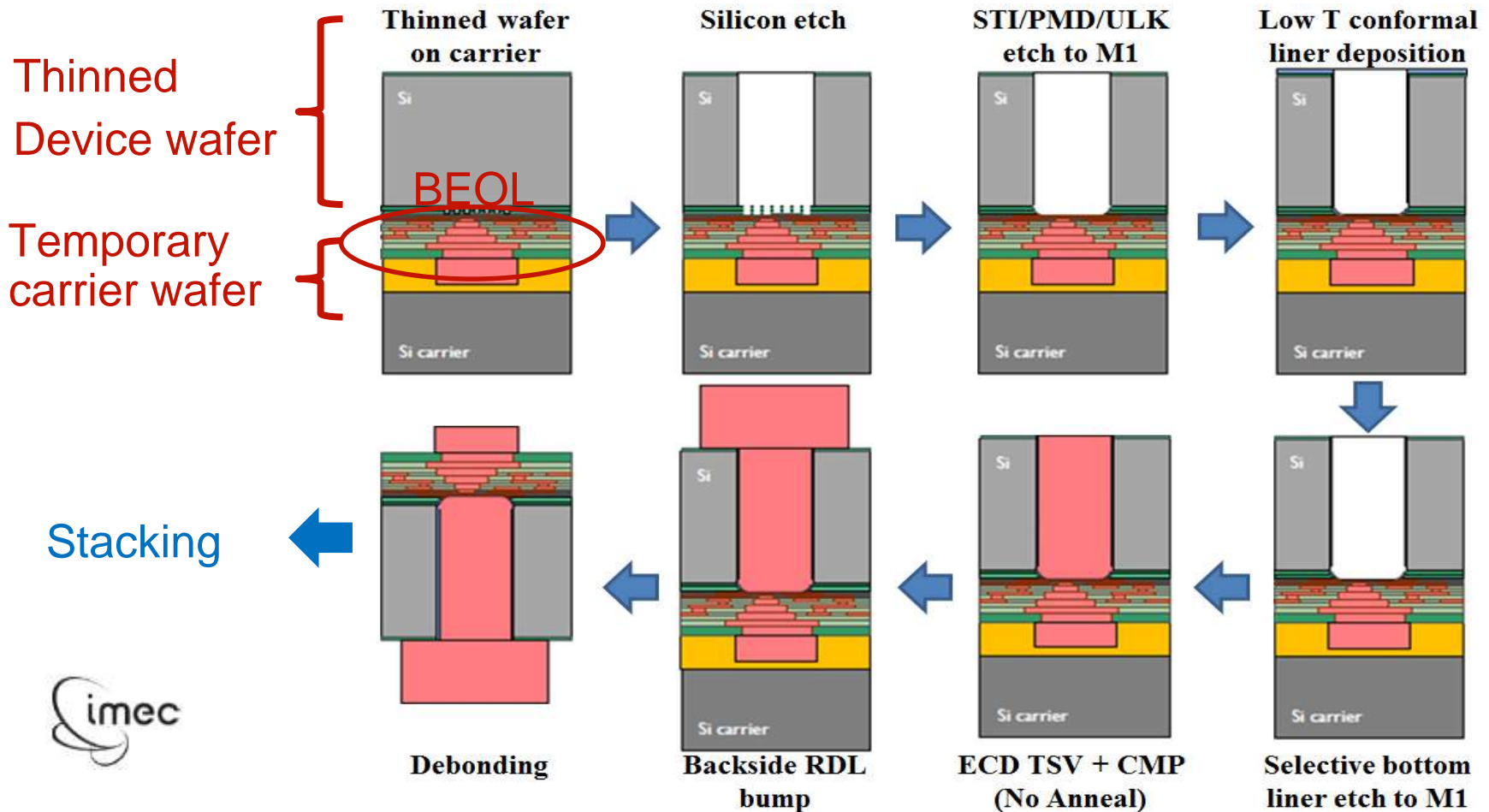
BEOL process

350°C SiCN Dep.
 320°C ULK Dep.
 400°C UV Cure
 400°C APF Dep.
 350°C SiOC/DARC Dep.
 400°C SiN Dep.

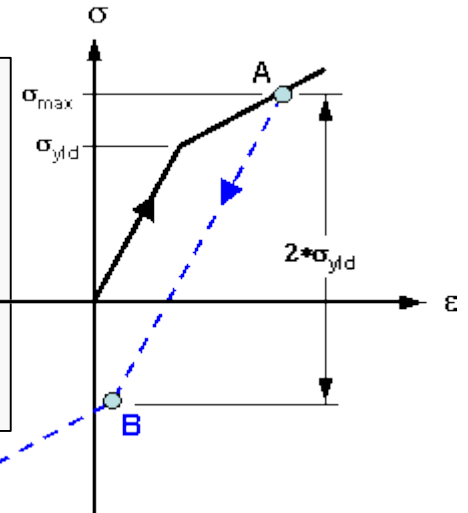
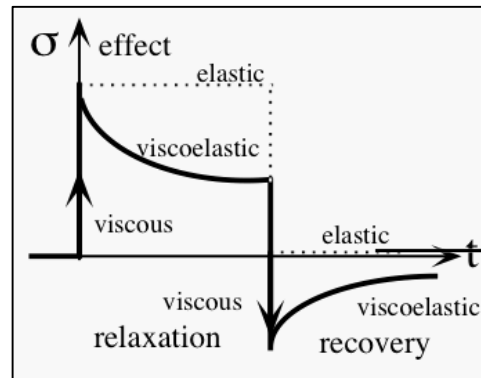
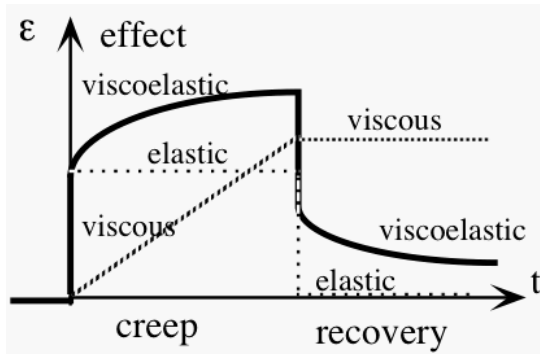
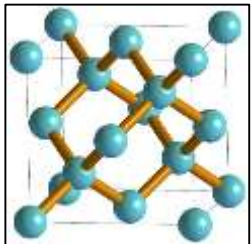
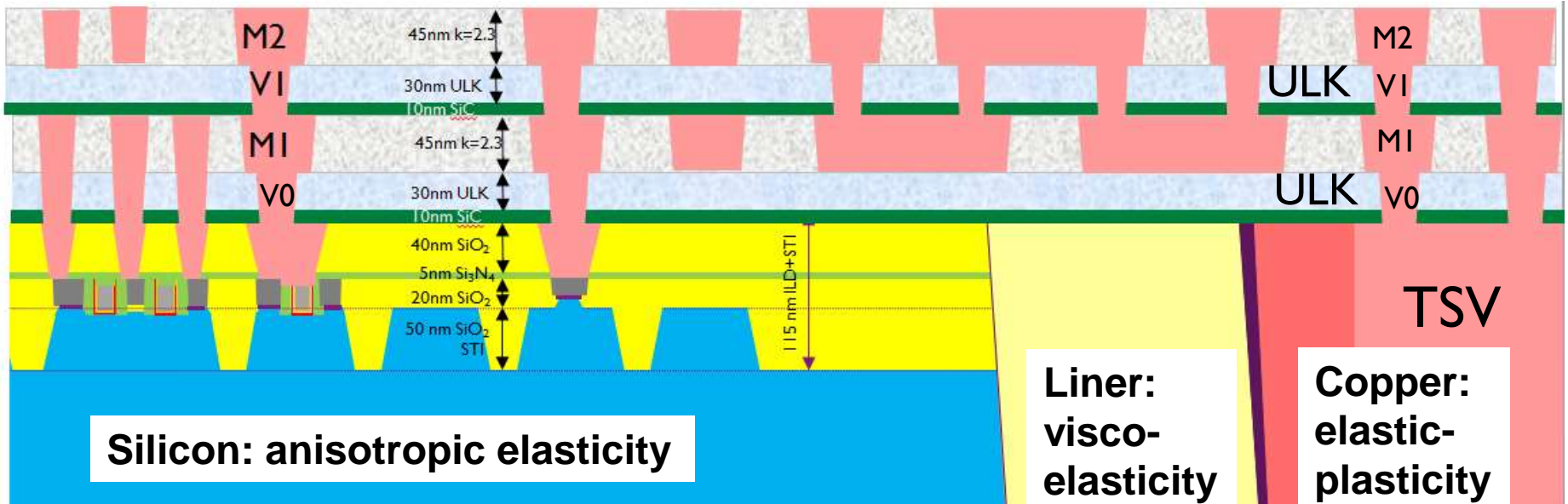


TSV-last Integration Sample Flow

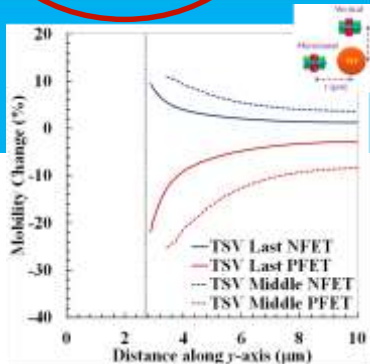
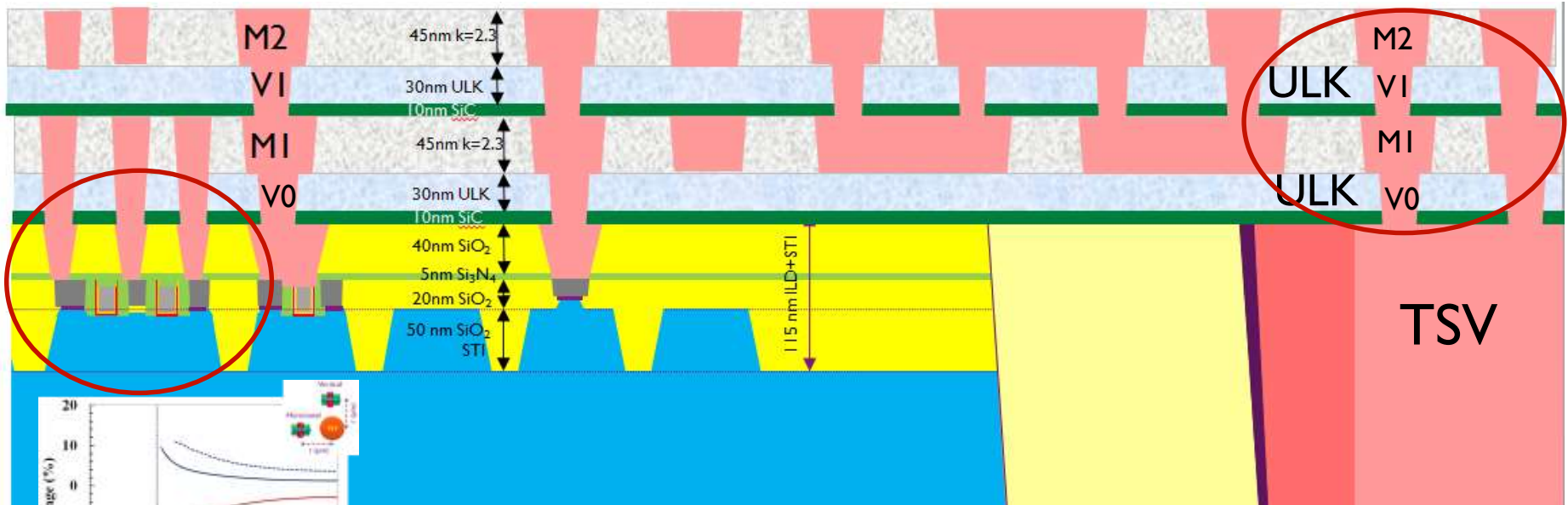
- TSV-last: via processed after FEOL and BEOL
- No high T budget is expected



Material Options



TSV Integration Considerations



FEOL performance

BEOL performance and reliability



Source: GlobalFoundries, ECTC 2015

- How TSV integration process and material options affect FEOL and BEOL
- Capabilities for analysis and optimization

Agenda

Introduction

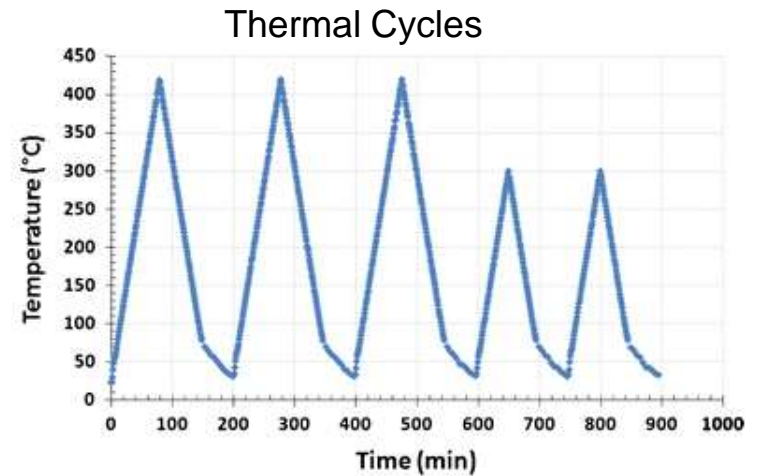
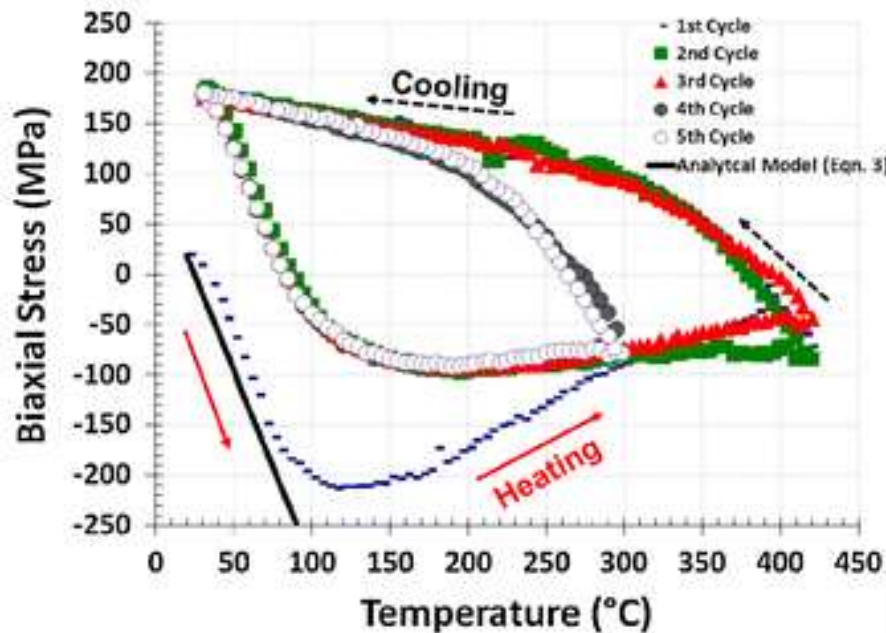
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TSV stress effects on performance and reliability

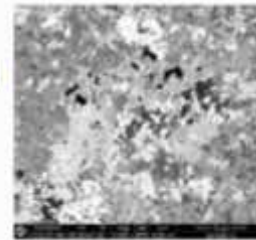
Summary

Copper Elastic-Plasticity Behavior

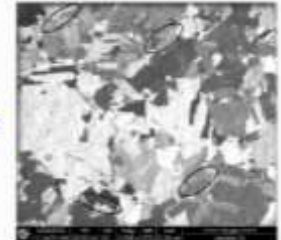
- Experimental Biaxial stress response of Cu film under thermal cycling



As deposited
Cu film



After
sintering
temperature
cycling



C. Okoro, et al., "Impact of the electrodeposition chemistry used for TSV filling on the microstructural and thermo-mechanical response of Cu," *Journal of Materials Science*, vol. 46, no. 11, pp. 3868 - 3882, June 2011.

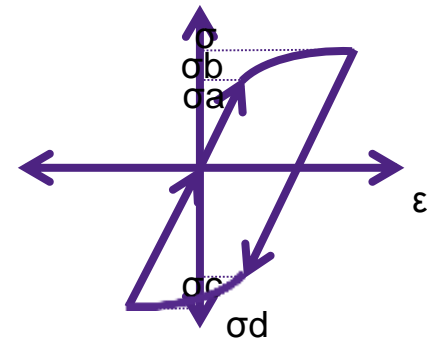
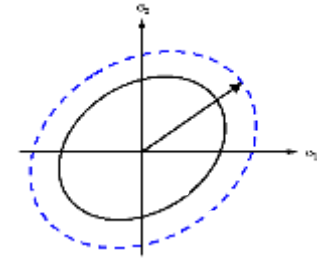
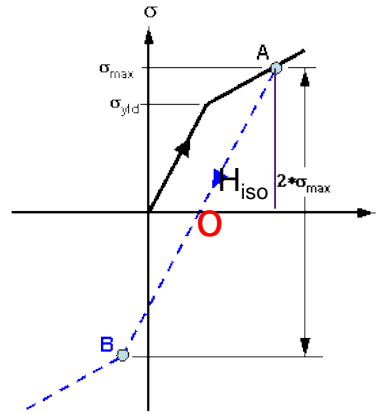
Nonlinear Plasticity with Isotropic and Kinematic Hardening

- Isotropic hardening

- Exponential hardening
- New yield stress:

$$\sigma_y = \sigma_{y0} + R[1 - \exp(-b\alpha)]$$

- Material parameters:
 - Initial yield stress (σ_{y0})
 - R
 - b

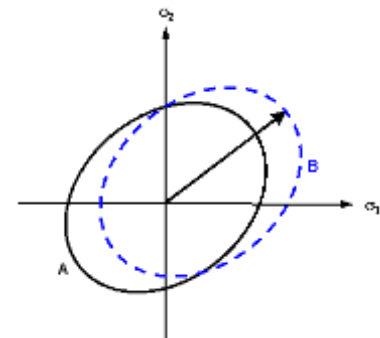
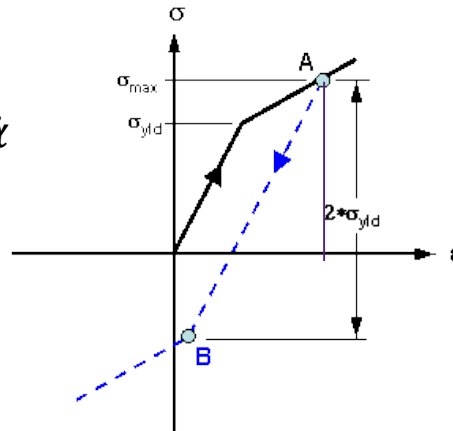


- Kinematic hardening

- Nonlinear hardening
- Back stress:

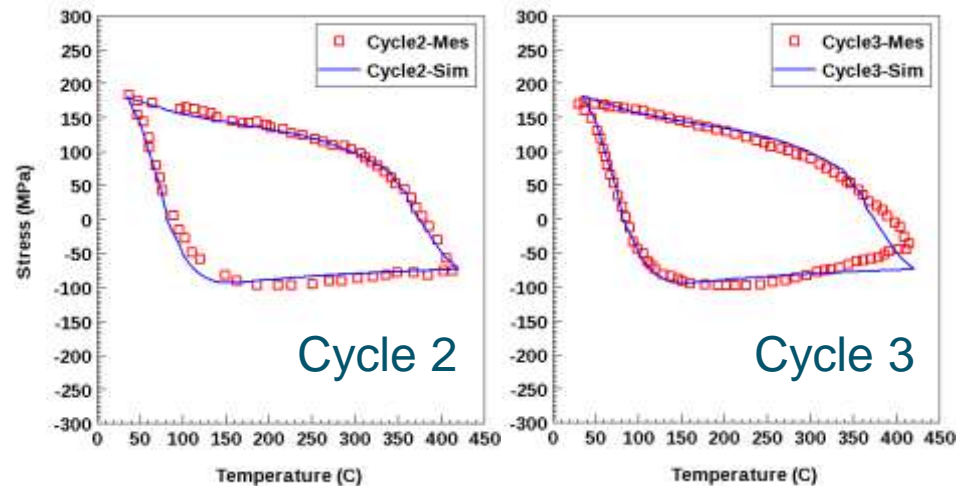
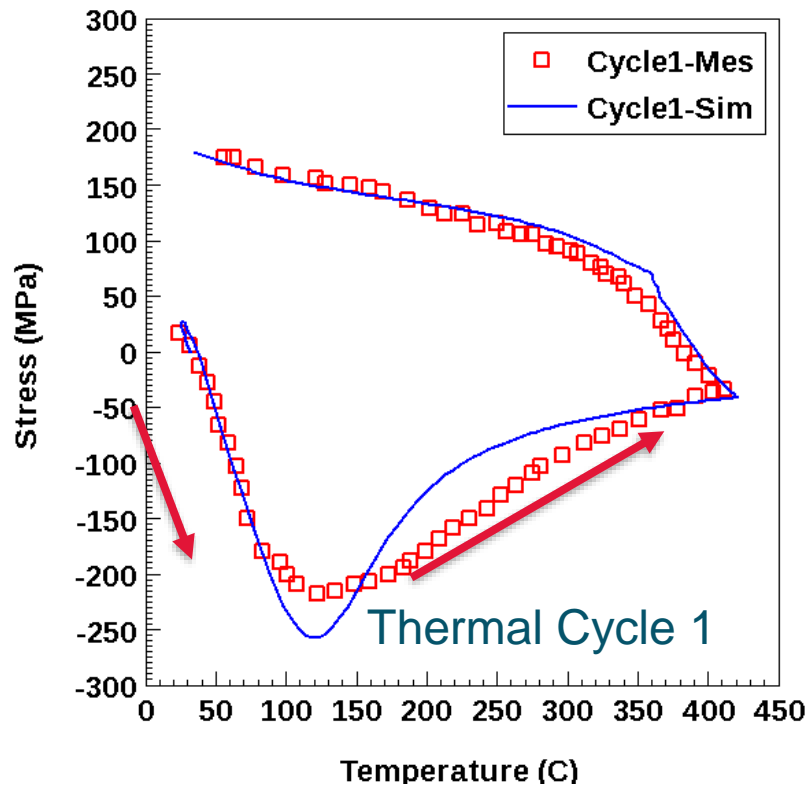
$$\dot{q}_{ij} = \left(H_{kin} n_{ij} - \sqrt{\frac{2}{3}} H_{kNL} q_{ij} \right) \dot{\alpha}$$

- Material parameters:
 - Hkin (H_{kin})
 - HNLkin (H_{kNL})



Elastic-Plasticity Model Calibration for Copper

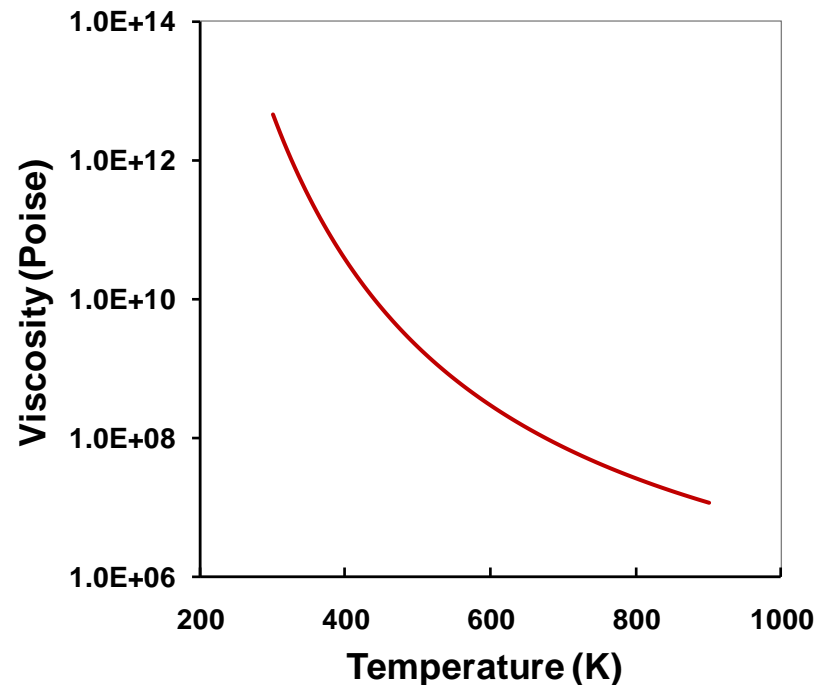
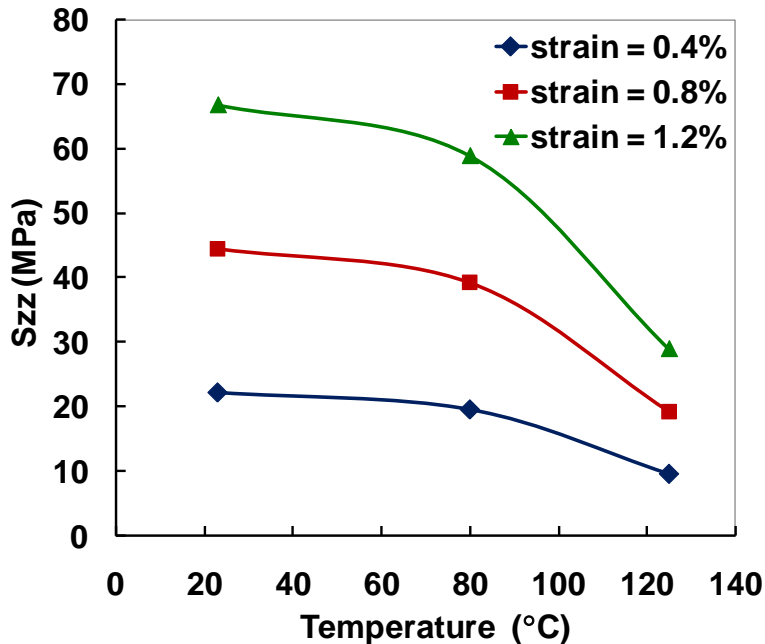
- Incremental plasticity model with nonlinear hardening can match measured data from thermal cycles



Cu stress highly depends on the thermal history of integration flow.

Dielectrics Visco-Elasticity Behavior

- Stress relaxation at elevated temperatures

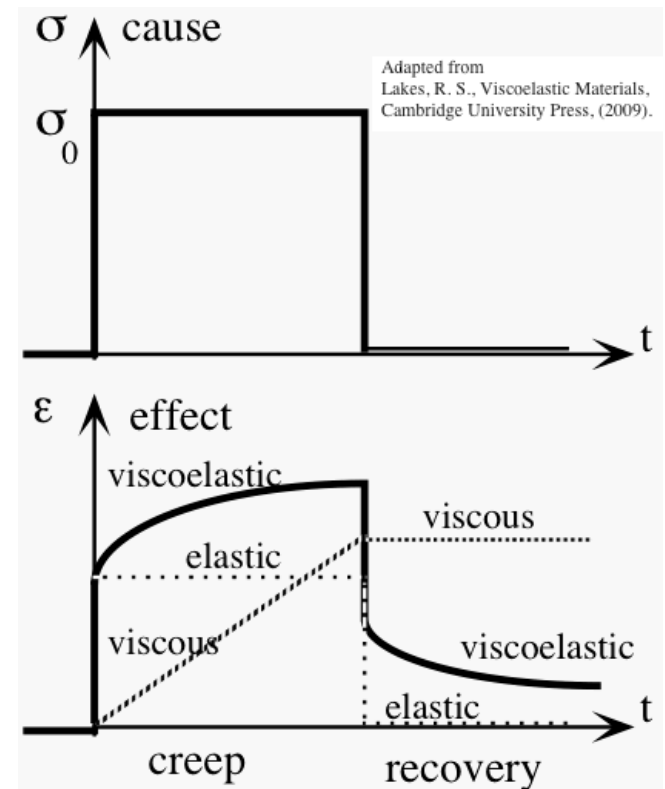
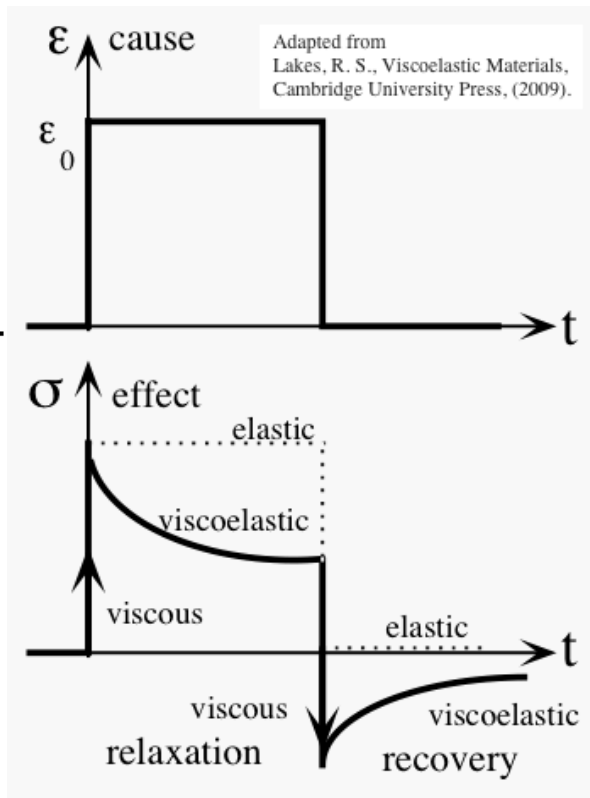
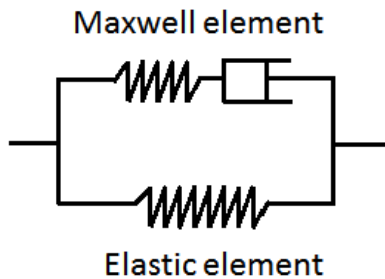


Liner stress highly depends on the thermal history of integration flow.

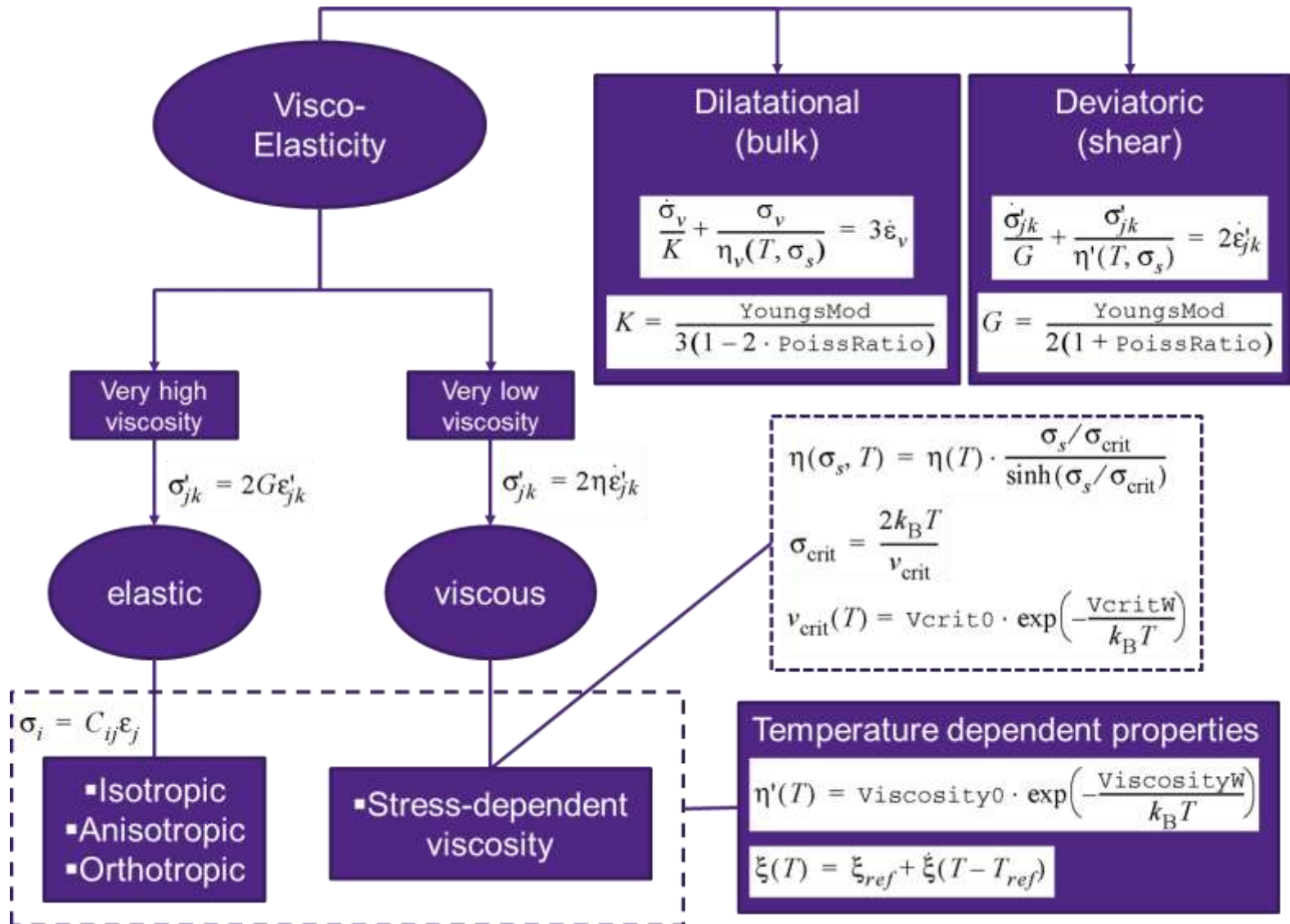
Nonlinear Visco-Elasticity Model with Stress Relaxation and Strain Creep

Relaxation

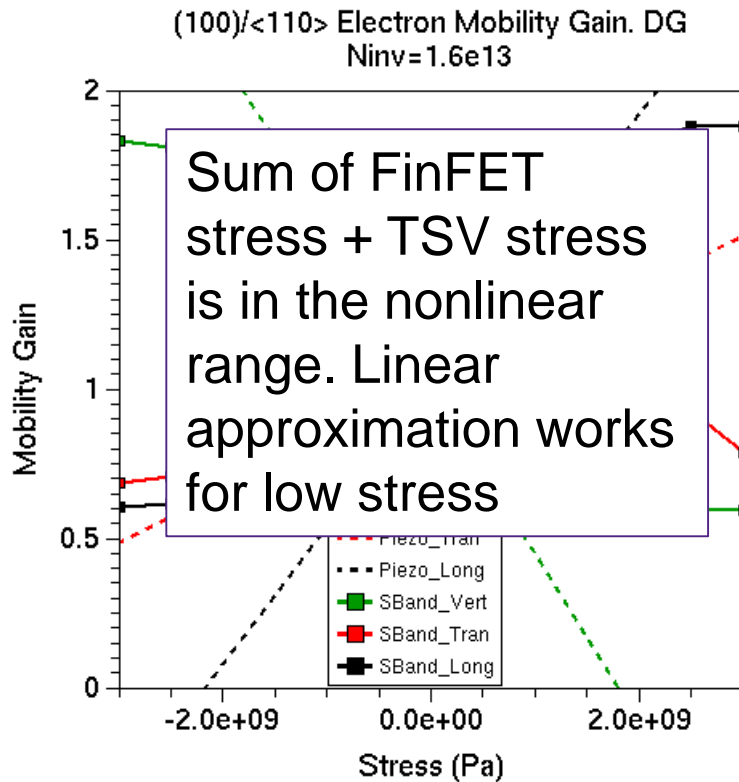
Creep



Visco-Elasticity Model Calibration for Liner

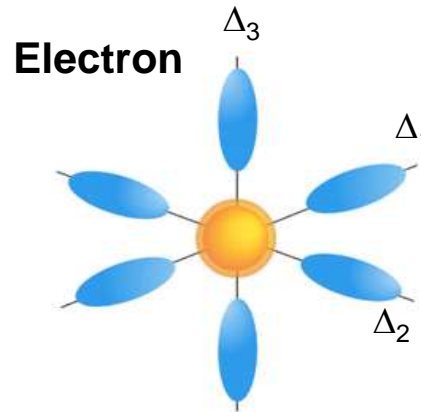


1st and 2nd Order Piezo-Resistance Models

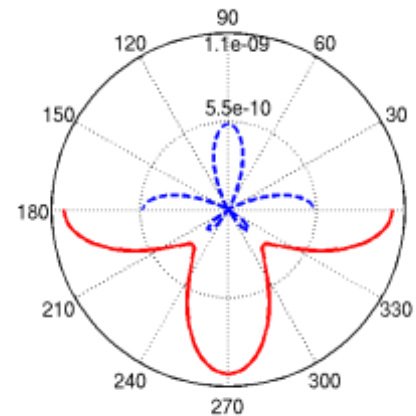
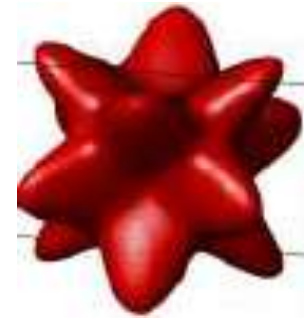


Piezo coefficients depend on crystal orientation, carrier type and stress magnitude

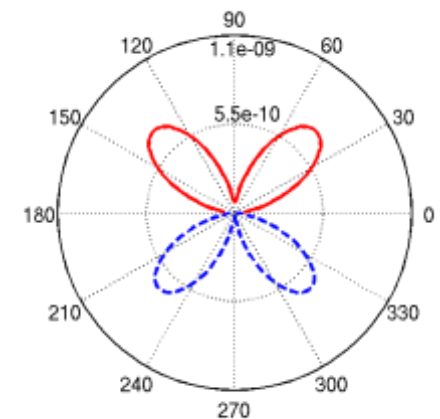
Band structure calculation



Hole



[001] Surface nMOS



[001] Surface pMOS

Agenda

Introduction

Material model characterization

TSV stress effects on performance and reliability

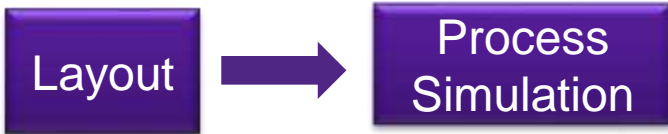
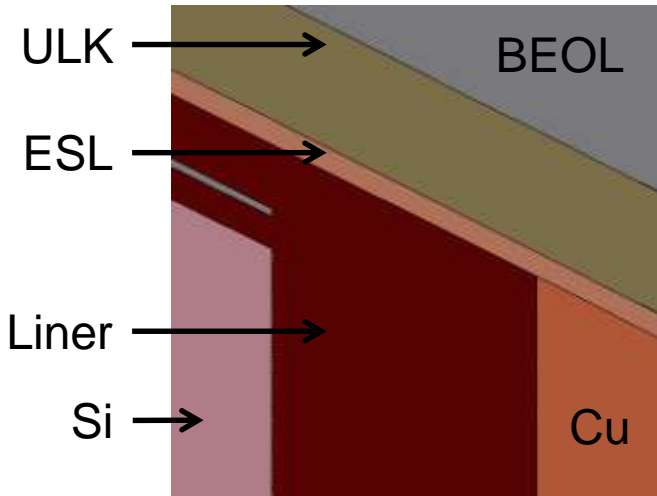
Summary

Test Case Descriptions

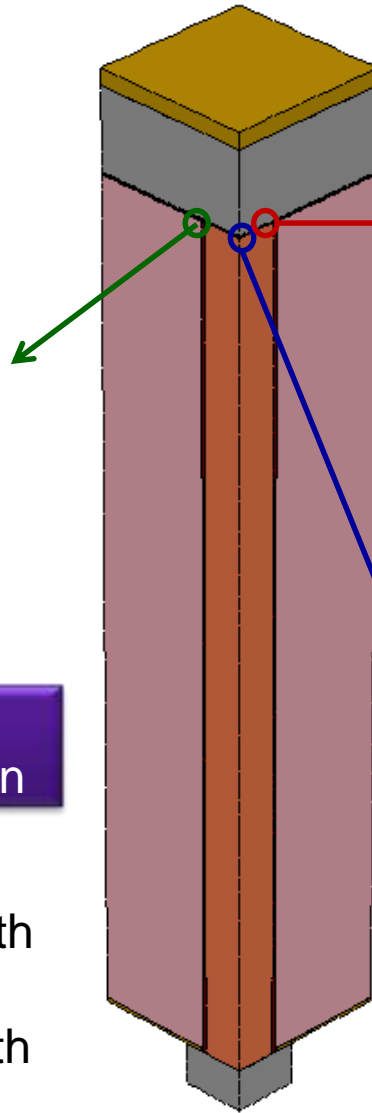
- Impact on FEOL performance
 - TSV middle versus TSV last
 - Plastic flow and viscous flow
- Impact on BEOL performance
 - TSV-middle versus TSV-last
 - Plastic flow and viscous flow
- Impact on BEOL Stress in TSV-last
 - M1 at TSV center versus M1 at TSV edge
 - Plastic flow and viscous flow

TSV Structures

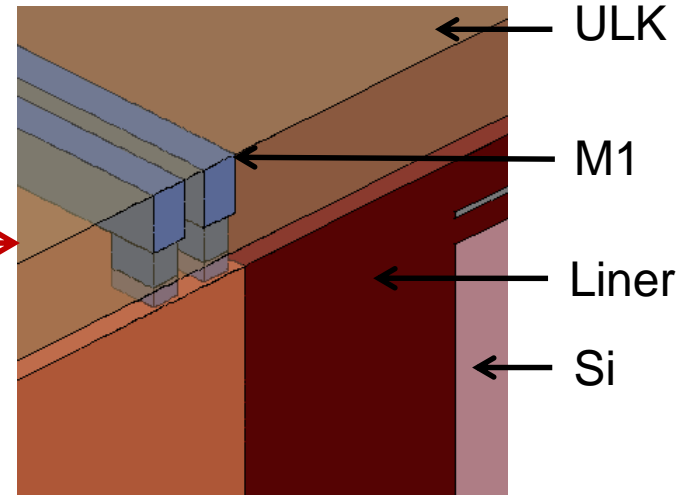
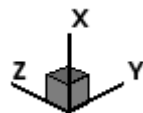
Liner structure near active silicon



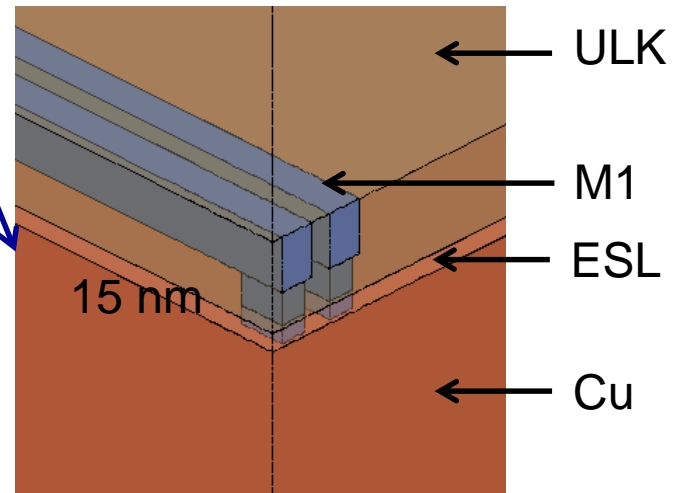
- Liner is modeled with visco-elasticity
- Copper is model with elastic-plasticity



TSV 5x50 um

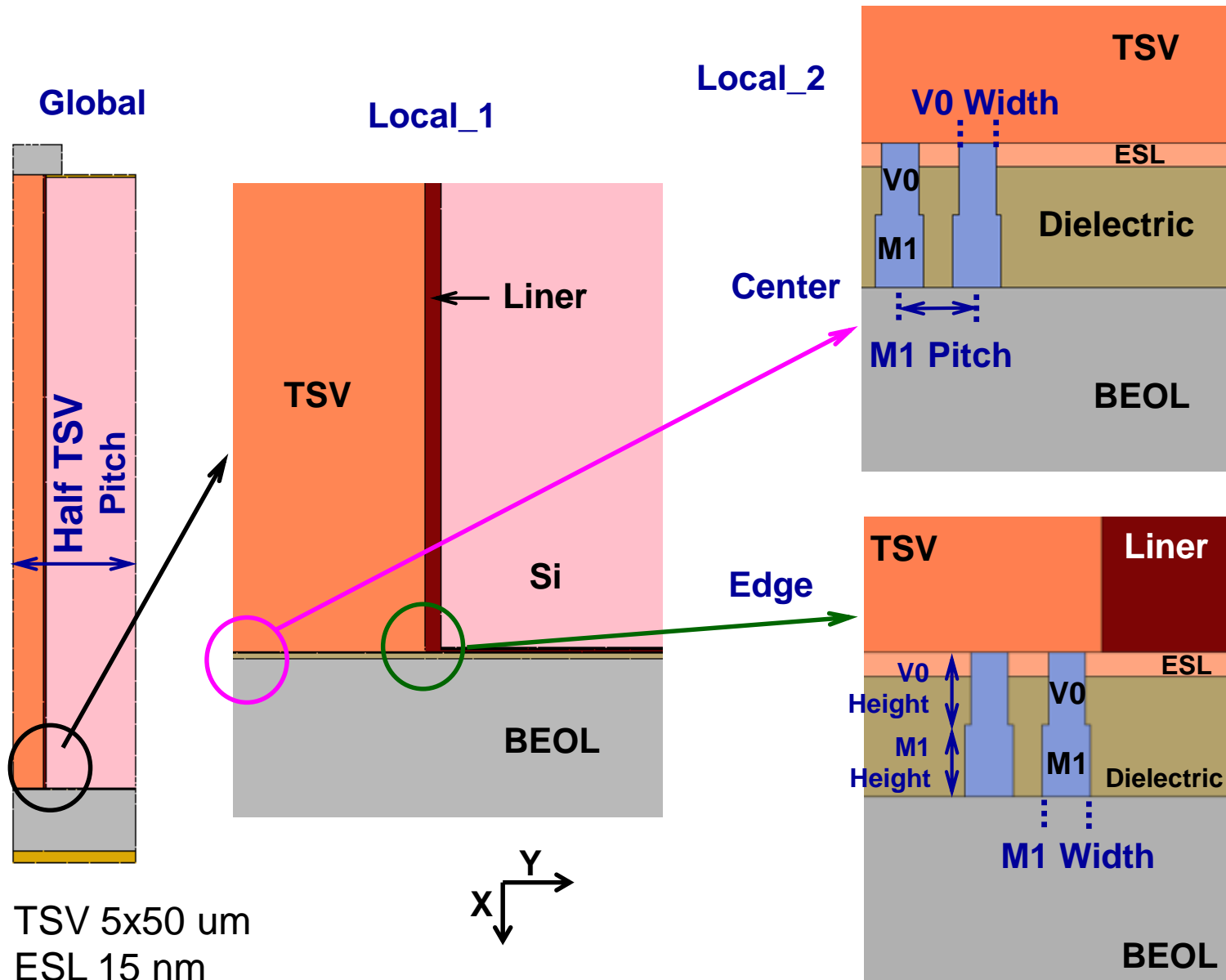


M1 at the edge of the TSV



M1 at the center of the TSV

Global and Local Models

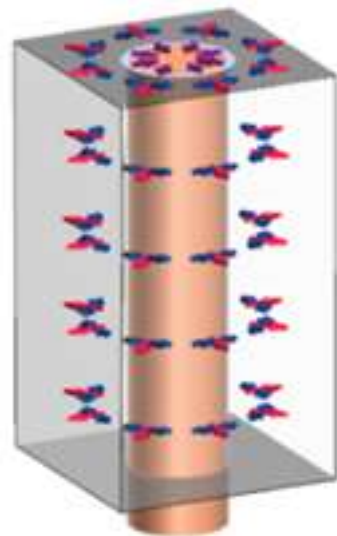


TSV 5x50 μm
ESL 15 nm

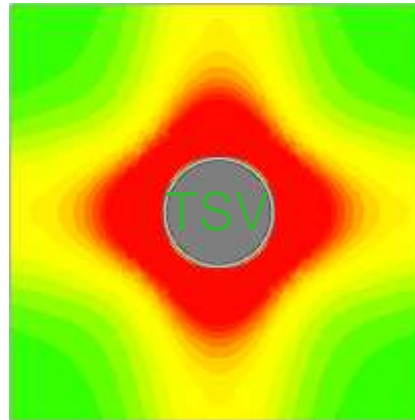
TSV Impact on FEOL:

TSV induced in-plane stress

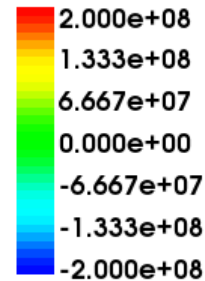
- TSV-last induces lower stress due to lower thermal budget



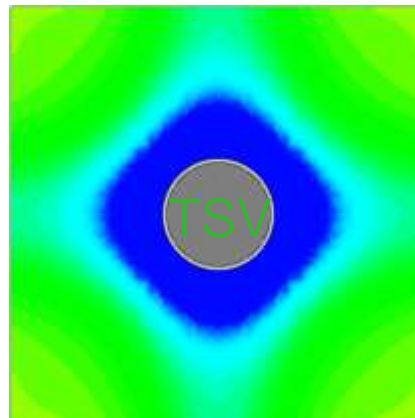
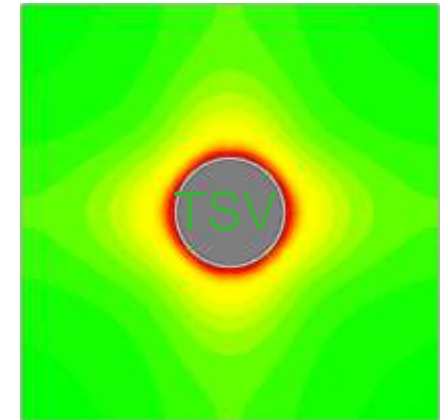
TSV-Middle



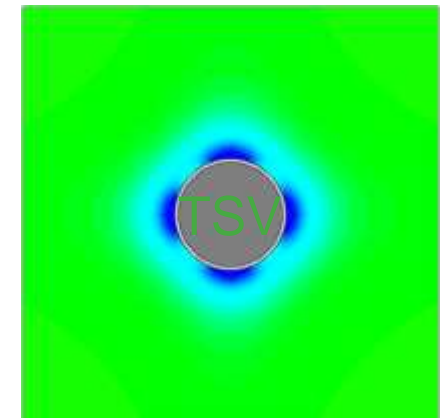
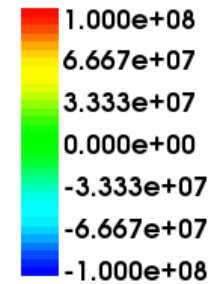
S_{Radial} (Pa)



TSV-Last



S_{Hoop} (Pa)



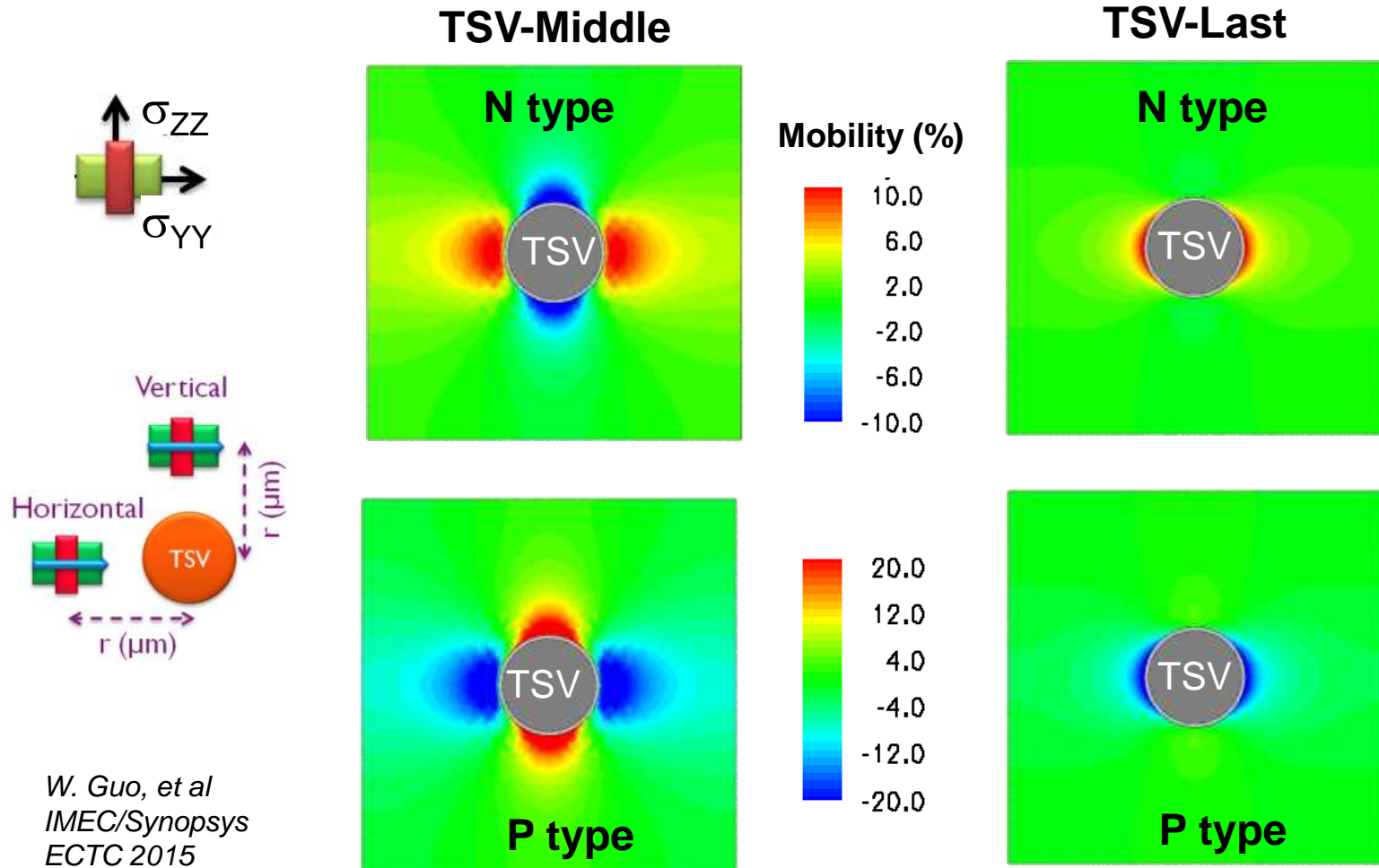
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Impact on FEOL:

Stress induced mobility change

- Device mobility change calculated for (100)/<110>

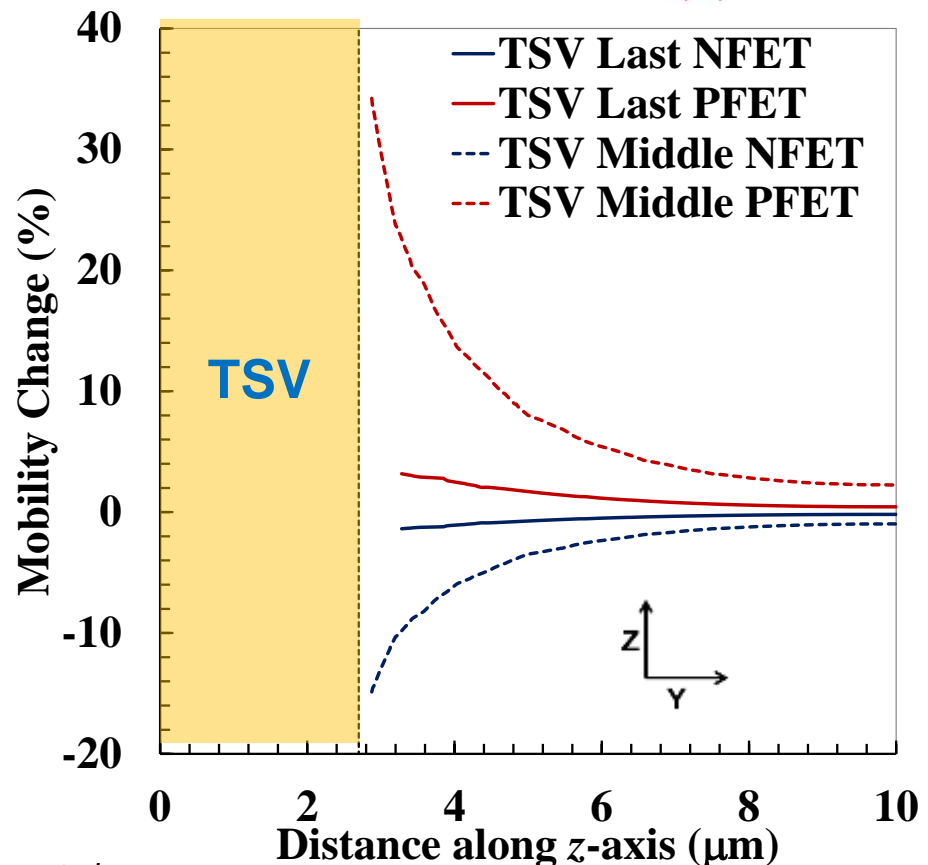
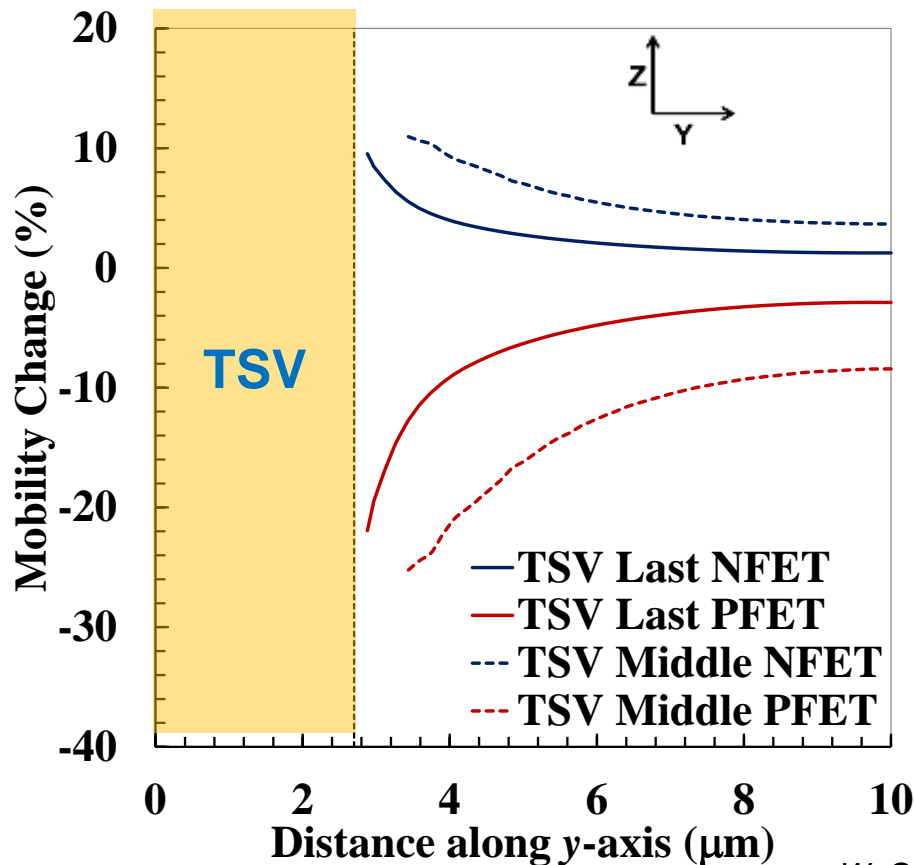
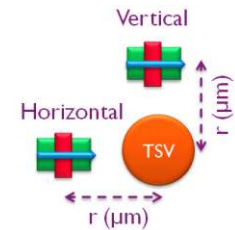


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Impact on FEOL

Stress induced mobility change

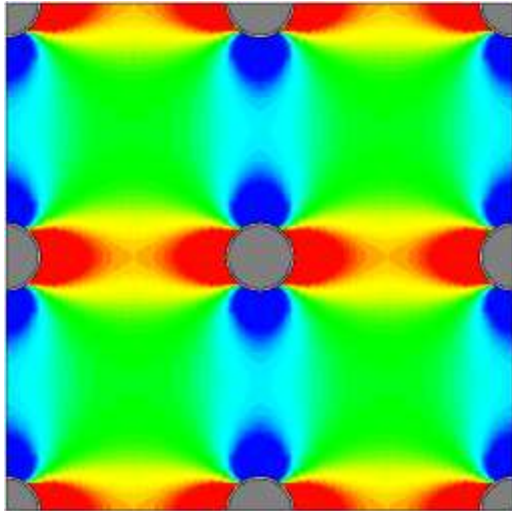
- Lower via-last stress affects less on mobility
- Impact on NFET is smaller compare to PFET



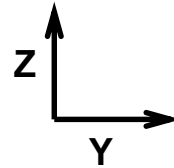
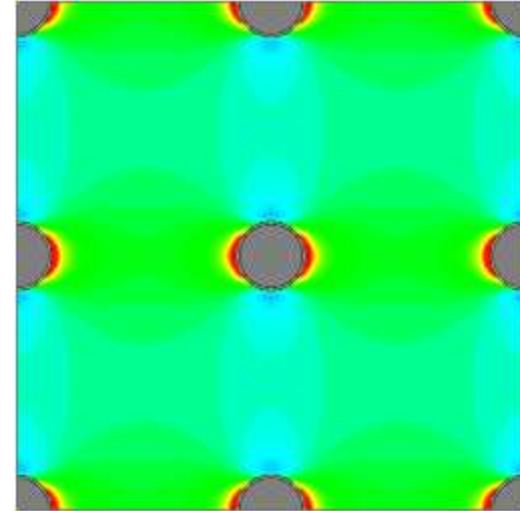
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Syy with Plastic or Plastic+Viscous Flow

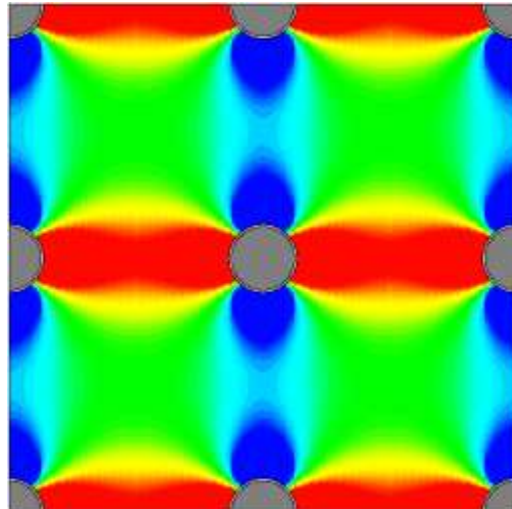
Plastic + viscous flow, TSV Middle



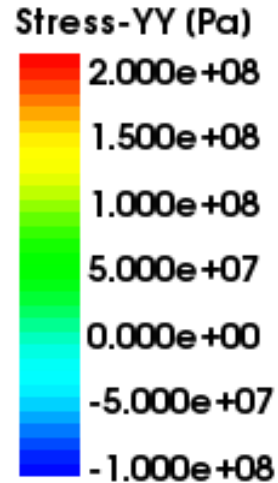
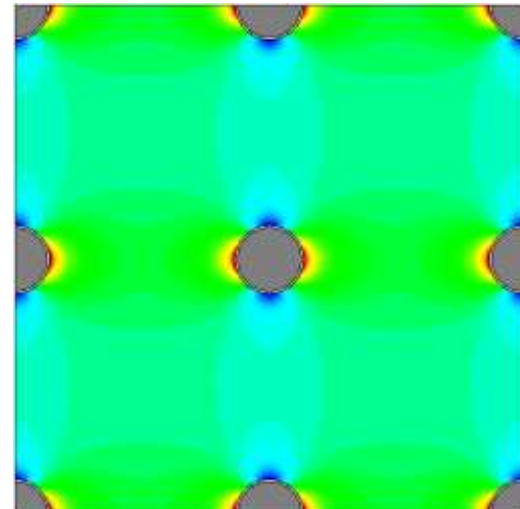
Plastic + viscous flow, TSV Last



Plastic flow, TSV Middle

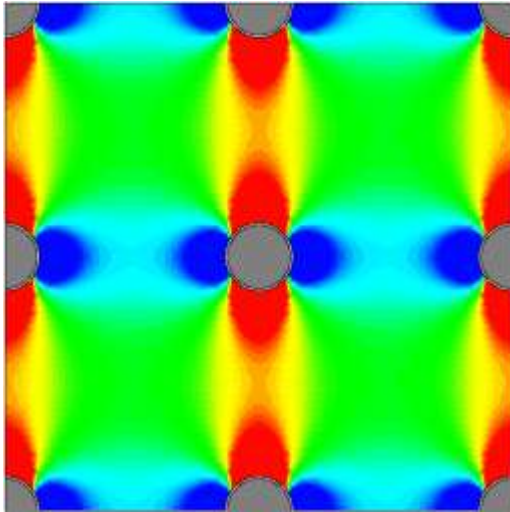


Plastic flow, TSV Last

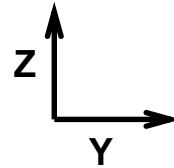
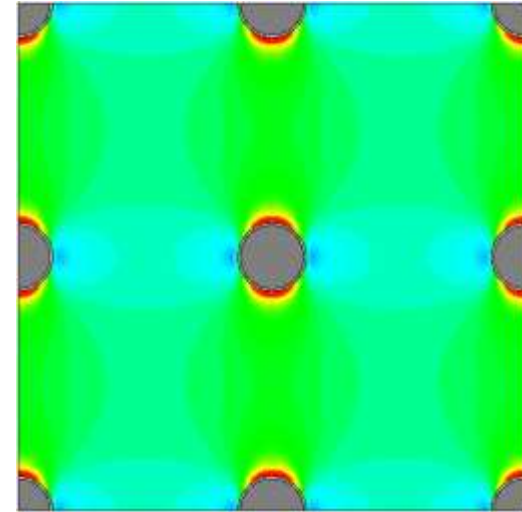


Szz with Plastic or Plastic+Viscous Flow

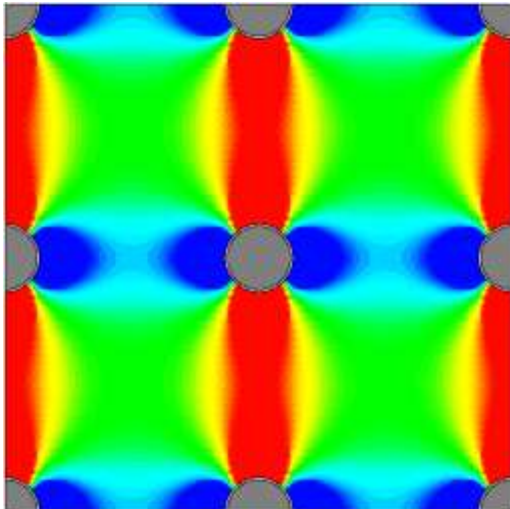
Plastic + viscous flow, TSV Middle



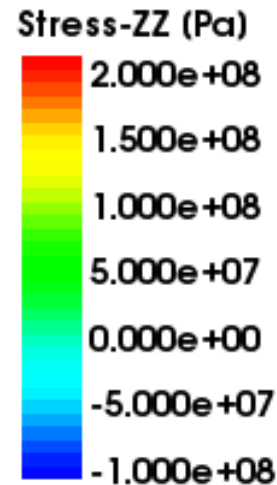
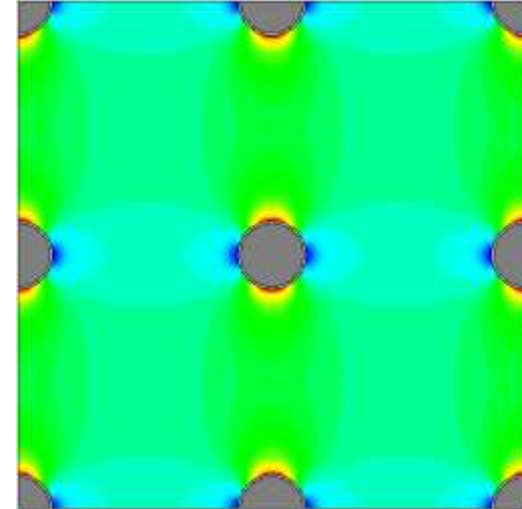
Plastic + viscous flow, TSV Last



Plastic flow, TSV Middle



Plastic flow, TSV Last



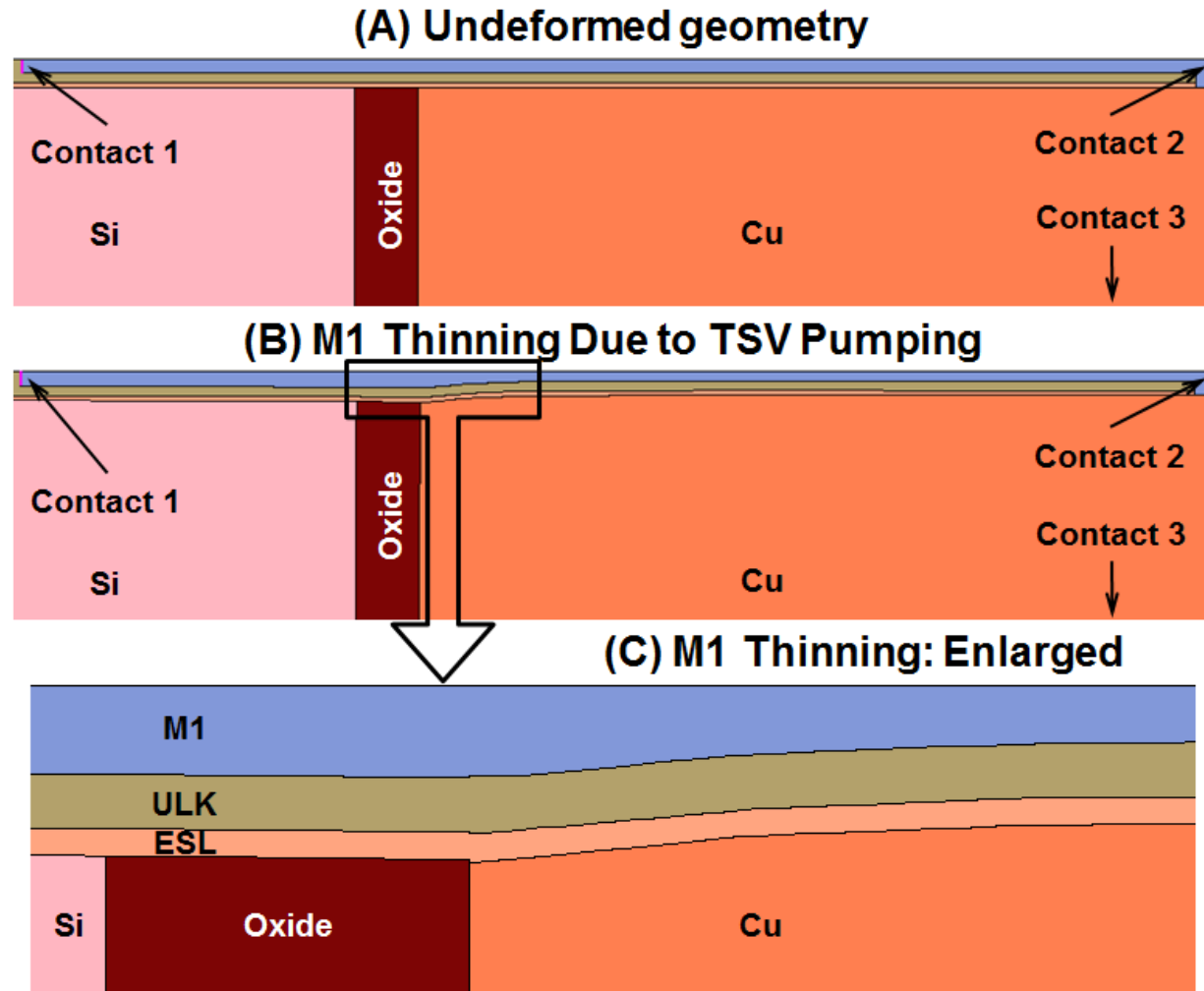
Test Case Descriptions

- Impact on FEOL performance
 - TSV middle versus TSV last
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- Impact on BEOL performance
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 - Plastic flow and viscous flow

TSV Pumping: TSV-middle vs TSV-last

M1 resistance change for TSV-middle process

- TSV pumping for TSV-middle due to high T BEOL
- 33% M1 resistance increases due to TSV plastic flow
- Additional 12% M1 resistance increase due to viscous flow
- No TSV pumping for TSV-last due to lower T budget

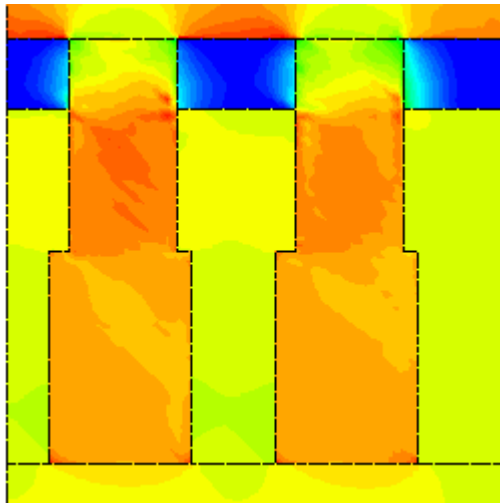


Test Case Descriptions

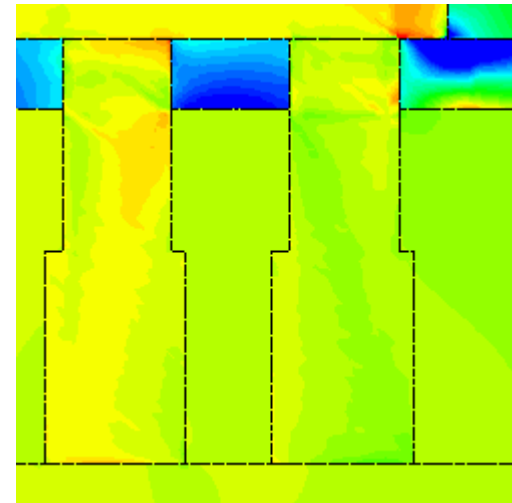
- Impact on FEOL performance
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- Impact on BEOL Stress in TSV-last
 - M1 at TSV center versus M1 at TSV edge
 - Plastic and viscous flow versus no flow

BEOL Hydrostatic Stress in TSV-last

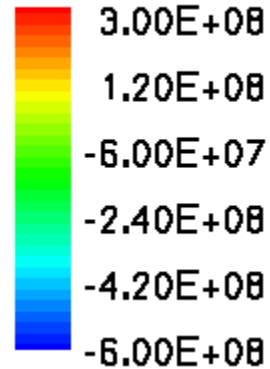
Plastic + viscous flow, Center



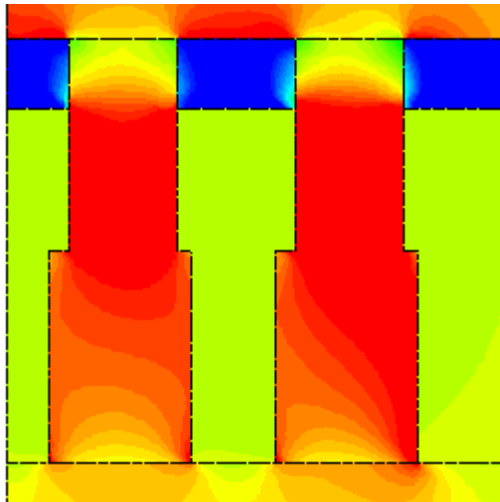
Plastic + viscous flow, Edge



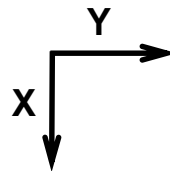
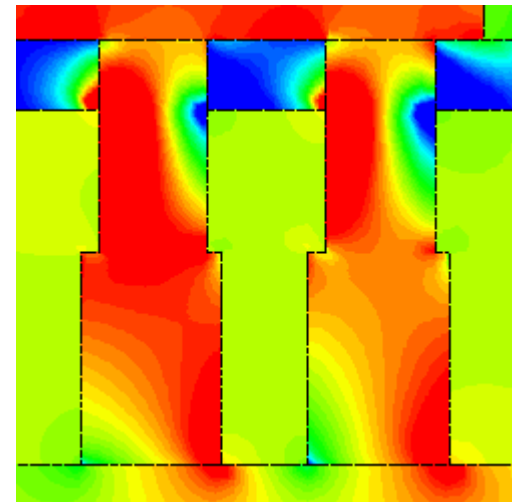
Hydrostatic [Pa]



No flow, Center

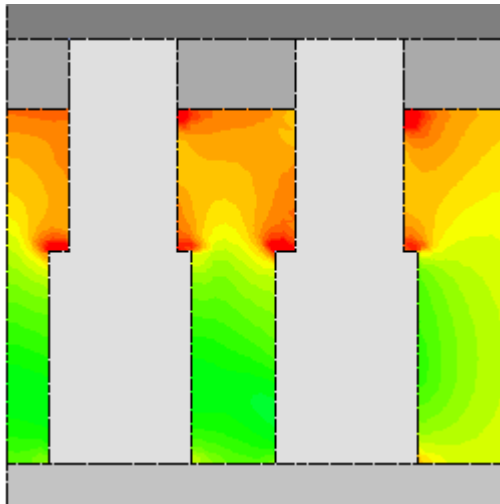


No flow, Edge

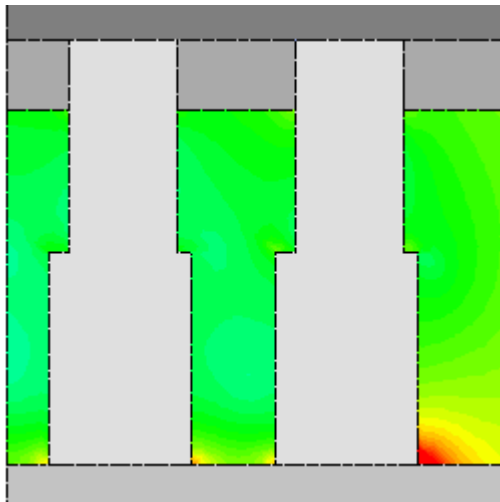


Dielectric 1st Principal Stress in TSV-last

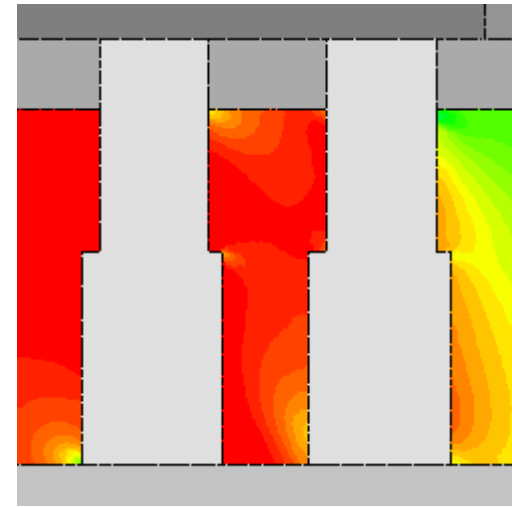
Plastic + viscous flow, Center



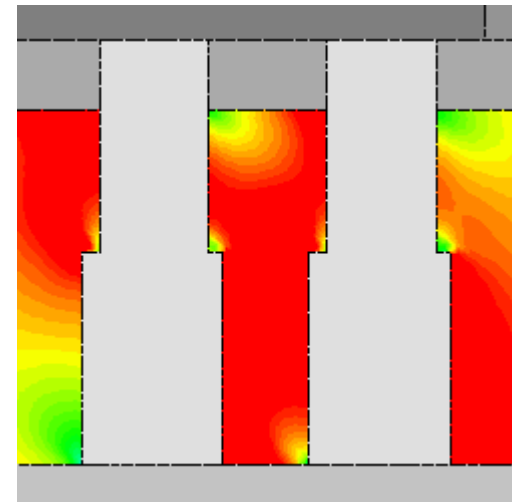
No flow, Center



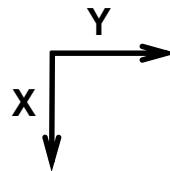
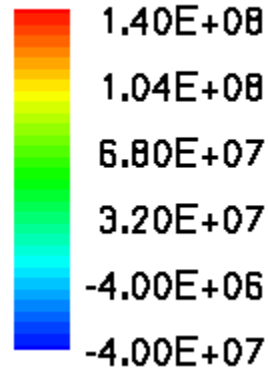
Plastic + viscous flow, Edge



No flow, Edge



PrincipalStress1 [Pa]



Summary

- Impact on FEOL performance
 - TSV-middle integration introduces larger residual stresses in active silicon compared to the TSV-last flow integration.
 - Plastic and viscous flow reduce silicon stress
- Impact on BEOL performance
 - TSV-middle integration results in M1 metal resistance increase due to copper pumping
 - Plastic and viscous flow increase TSV pumping
- Impact on BEOL stress
 - Residual stress profiles in BEOL structures are different for TSV middle and TSV last flows
- Ongoing work
 - TSV-last long term stability and reliability